

## **isc** Silicon NPN Power Transistor

# **BUX84**

### DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 400V(Min.)
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

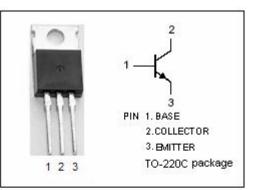
Designed for use in high-voltage, high-speed, power switching regulators, converters, inverters, motor control system.

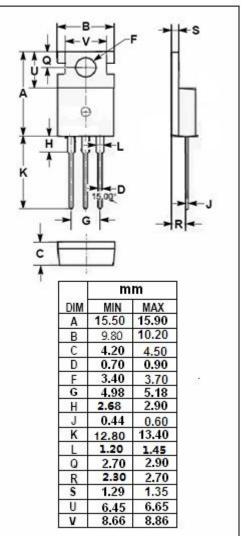
### ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CES</sub>	Collector-Emitter Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
lc	Collector Current-Continuous	Current-Continuous 2	
I <sub>CM</sub>	Collector Current-Peak	3	А
I <sub>B</sub>	Base Current	0.75	А
I <sub>BM</sub>	Base Current-Peak	1	А
Pc	Collector Power Dissipation @Tc=25°C	40	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.5	°C/W





isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	400			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.3A; I <sub>B</sub> = 0.03A			0.8	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.1	V
І <sub>сво</sub>	Collector Cutoff Current	$V_{CB}$ = 800V; I <sub>E</sub> = 0 $V_{CB}$ = 800V; I <sub>E</sub> = 0;T <sub>C</sub> =125 °C			0.2 1.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	20		100	
h <sub>FE-2</sub>	DC Current Gain	Ic= 0.5A; Vce= 5V	15			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V, f <sub>test</sub> = 1MHz		20		MHz

### **NOTICE:**

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